

**INFORMATION  
DISCLOSURE  
STATEMENT**

Atty. Docket No.: 150.00880103

Serial No.: 10/045,345

Applicant(s): Derderian et al.

Confirmation No.: 1310

Application Filing Date: 25 October 2001

Group: 2818

Information Disclosure Statement mailed: December 12, 2002

**U.S. PATENT DOCUMENTS**

Examiner Initial	Copy Enclosed	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
PD	X	6,337,238	01/08/02	Nakabayashi			

**FOREIGN PATENT DOCUMENTS**

Examiner Initial	Copy Enclosed	Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
		None						

**OTHER DOCUMENTS (Including Authors, Title, Date, Pertinent Papers, etc.)**

Examiner Initial	Copy Enclosed	Document Description
		None

RECEIVED  
DEC 20 2002  
TECHNICAL SERVICES DIVISION

<b>EXAMINER</b> PHUC T. DANG	<b>Date Considered</b> 7/18/2003
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

<b>INFORMATION DISCLOSURE STATEMENT</b>	<b>Atty. Docket No.:</b> 150.0088 0103	<b>Serial No.:</b> 10/045,345
	<b>Applicant(s):</b> Derderian et al.	<b>Confirmation No.:</b>
	<b>Filing Date:</b> 25 October 2001	<b>Group:</b> 2818

Examiner Initial	Copy Enclosed	Document Description
PD ↑		Nakamura et al., "Embedded DRAM Technology compatible to the 0.18μm high-speed Logics by using Ru pillars in cell capacitors and peripheral vias," <i>J. Electrochem. Soc.</i> , 147:203-209 (1998).
		Park et al., "Metallorganic Chemical Vapor Deposition of Ru and RuO <sub>2</sub> Using Ruthenocene Precursor and Oxygen Gas," <i>J. Electrochem. Soc.</i> , 147:203-209 (2000).
		Senzaki et al., Chemical Abstract 128:264103, <i>Proc. Electrochem. Soc.</i> , 97-25 (Chemical Vapor Deposition), 933-43 (1997).
		Shin, "Characterization of RuO <sub>2</sub> Thin Films Prepared by Hot-Wall Metallorganic Chemical Vapor Deposition," <i>J. Electrochem. Soc.</i> , 144, 1055 (1997).
		Sosinsky et al., "Hydrocarbon Complexes of Ruthenium. Part IV. Cyclic Dienyl Complexes", <i>J. Chem. Soc.</i> , 16-17, 1633-1640 (1975).
		Takagi et al., "RuO <sub>2</sub> Bottom Electrodes for Ferroelectric (Pb, La)(Zr, Ti)O <sub>3</sub> Thin Films by Metallorganic Chemical Vapor Deposition", <i>Jpn. J. Appl. Phys.</i> , 34, 4104-4107 (1995).
		Versteeg et al., "Metalorganic Chemical Vapor Deposition By Pulsed Liquid Injection Using An Ultrasonic Nozzle: Titanium Dioxide on Sapphire from Titanium (IV) Isopropoxide," <i>Journal of the American Ceramic Society</i> , 78, 2763-2768 (1995).
		Yuan, "Low-Temperature Chemical Vapor Deposition of Ruthenium Dioxide from Ruthenium Tetroxide: A Simple Approach to High-Purity RuO <sub>2</sub> Films," <i>Chem. Mater.</i> , 5, 908 (1993).
PD ↓		Yang, Doo Young et al., "Characterization of Ru Electrodes for Ru/(Ba,Sr)TiO <sub>3</sub> /Ru Capacitors," <i>Ferroelectrics</i> , 1996. ISAF '96: Proceedings of the Tenth IEEE International Symposium on Applications of Ferroelectrics" New York, NY, August 18, 1996; pgs. 515-518.

<b>EXAMINER</b>  PHUC T. DANG	<b>Date Considered</b>  7/18/2003
*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	